

A.S.D.™

LCP1521 PROGRAMMABLE TRANSIENT VOLTAGE SUPPRESSOR FOR SLIC PROTECTION

# FEATURES

- Dual programmable transient suppressor
- Wide negative firing voltage range:
  V<sub>MGL</sub> = -150 V max.
- Low dynamic switching voltages: V<sub>FP</sub> and V<sub>DGL</sub>
- Low gate triggering current: I<sub>GT</sub> = 5 mA max
- Peak pulse current:  $I_{PP} = 30 \text{ A} (10/1000 \text{ } \mu\text{s})$
- Holding current: I<sub>H</sub> = 150 mA min

#### DESCRIPTION

This device has been especially designed to protect new high voltage, as well as classical SLICs, against transient overvoltages.

Positive overvoltages are clamped by 2 diodes. Negative surges are suppressed by 2 thyristors, their breakdown voltage being referenced to  $-V_{\text{BAT}}$  through the gate.

This component presents a very low gate triggering current ( $I_{GT}$ ) in order to reduce the current consumption on printed circuit board during the firing phase.

A particular attention has been given to the internal wire bonding. The Kelvin method congutation ensures reliable protection, reducing the overvoltage introduced by the parasitic inductances of the wiring, especially for very fast transients.

#### BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. Tricits are used to help equipment to meet various standards such as UL1950, IEC950 / CSA C22.2, UL1459 and FCC part68. Trisils have UL94 V0 resin approved (Trisils are UL497B approved (file: E136224)).



#### **VUNCTIONAL DIAGRAM**



# LCP1521

# IN COMPLIANCES WITH THE FOLLOWING STANDARDS

STANDARD	Peak Surge Voltage (V)	Voltage Waveform	Required peak current (A)	Current Waveform	Minimum serial resistor to mee standard (Ω)			
GR-1089 Core First level	2500 1000	2/10µs 10/1000µs	500 100	2/10µs 10/1000µs	10 24			
GR-1089 Core Second level	5000	2/10µs	500	2/10µs	20			
GR-1089 Core Intra-building	1500	2/10µs	100	2/10µs	0			
ITU-T-K20/K21	6000 1500	10/700µs	150 37.5	5/310µs	110 0			
ITU-T-K20 (IEC61000-4-2)	8000 15000	1/60 ns	ESD contact ESD air di		0 0			
VDE0433	4000 2000	10/700µs	100 50	5/310µs	60 10			
VDE0878	4000 2000	1.2/50µs	100 50	1/20µs	05			
IEC61000-4-5	4000 4000	10/700µs 1.2/50µs	100 100	5/310µs 8/20µs	60 0			
FCC Part 68, lightning surge type A	g 1500 800	10/160µs 10/560µs	200 100	10/160µs 10/560µs	22.5 15			
FCC Part 68, lightning surge type B	g 1000	9/720µs	25	5/320µs	0			
THERMAL RESISTANCE								
Symbol	Valı	ie Unit						

#### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	170	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>amb</sub> = 25°C)

Parameter
Gate triggering current
Holding current
Reverse leakage current LINE / GND
Reverse leakage current GATE / LINE
Reverse voltage LINE / GND
Gate triggering voltage
Forward drop voltage LINE / GND
Peak forward voltage LINE / GND
Dynamic switching voltage GATE / LINE
GATE / GND voltage
Reverse voltage GATE / LINE
Capacitance LINE / GND



Symbol	Parameter		Value	Unit
Ірр	Peak pulse current (see note1)	10/1000μs 8/20μs 10/560μs 5/310μs 10/160μs 1/20μs 2/10μs	30 100 35 40 50 100 170	A
I <sub>TSM</sub>	Non repetitive surge peak on-state current (50Hz sinusoidal)	t = 10ms t = 1s	20 5	A
I <sub>GSM</sub>	Maximum gate current (50Hz sinusoidal)	t = 10ms	2	A
V <sub>MLG</sub> V <sub>MGL</sub>	Maximum voltage LINE/GND Maximum voltage GATE/LINE	-40°C < Tamb < +85°C -40°C < Tamb < +85°C	-150 -150	V
T <sub>stg</sub> Tj	Storage temperature range Maximum junction temperature		- 55 to + 150 150	S°C
TL	Maximum lead temperature for solde	260	°C	

ABSOLUTE RATINGS (T<sub>amb</sub> = 25°C, unless otherwise specified).

#### Repetitive peak pulse current

tr: rise time ( $\mu$ s) tp: pulse duration ( $\mu$ s) ex: Pulse waveform 10/1000 $\mu$ s tr = 10 $\mu$ s tp = 1000 $\mu$ s



### 1- PARAMETERS RELATED TO THE DIODE LINE / GND ( $T_{amb} = 25^{\circ}C$ )

Symbol	X	Test condition	Мах	Unit	
VF	I <sub>F</sub> = 5A		t = 500µs	2	V
V <sub>FP</sub> (note 1)	10/700μs 1.2/50μs 2/10μs	1.5kV 1.5kV 2.5kV	$\begin{array}{l} R_{\mathrm{s}}=10\Omega\\ R_{\mathrm{s}}=10\Omega\\ R_{\mathrm{s}}=62\Omega \end{array}$	5 7 12	V

Note 1: see test circuit for VFP; RS is the protection resistor located on the line card.

### LCP1521

#### 2 - PARAMETERS RELATED TO THE PROTECTION THYRISTOR (Tamb = 25°C unless otherwise specified)

Symbol	Test conditions		Min	Мах	Unit
I <sub>GT</sub>	$V_{\text{gND/LINE}} = -48V$		0.1	5	mA
IH	V <sub>GATE</sub> = -48V (note 2)		150		mA
V <sub>GT</sub>	at I <sub>gt</sub>			2.5	V
I <sub>RG</sub>	V <sub>RG</sub> = -150V V <sub>RG</sub> = -150V	Tc=25°C Tc=85°C		5 50	μA
V <sub>DGL</sub>	V <sub>GATE</sub> = -48V (note 3)				
	$\begin{array}{ccc} 10/700 \mu s & 1.5 kV & R_s = 10 \Omega \\ 1.2/50 \mu s & 1.5 kV & R_s = 10 \Omega \\ 2/10 \mu s & 2.5 kV & R_s = 62 \Omega \end{array}$	$I_{PP} = 30A$ $I_{PP} = 30A$ $I_{PP} = 38A$		7 10 25	V

Note 2: see functional holding current (IH) test circuit

Note 3: see test circuit for VDGL

The oscillations with a time duration lower than 50ns are not taken into account

# **3 - PARAMETERS RELATED TO DIODE AND PROTECTION THYRISTOR** ( $T_{amb} = 25^{\circ}C$ , unless otherwise specified)

Symbol	Test conditions	Тур.	Max.	Unit	
I <sub>RM</sub>	$ \begin{array}{l} V_{\text{gate/line}} = -1V & V_{\text{rm}} = -150V \\ V_{\text{gate/line}} = -1V & V_{\text{rm}} = -150V \end{array} $	Tc=25°C Tc=85°C	6	5 50	μA
С	$V_{R} = 50V$ bias, $V_{RMS} = 1V$ , F = 1MHz $V_{R} = 2V$ bias, $V_{RMS} = 1V$ , F = 1MHz	SOID	30 70		pF
05019	ete Producils)				

4/9

# FUNCTIONAL HOLDING CURRENT (I<sub>H</sub>) TEST CIRCUIT : GO-NO GO TEST



# **TEST PROCEDURE :**

- Adjust the current level at the I<sub>H</sub> value by short circuiting the D.U.T. Fire the D.U.T. with a surge current :  $I_{PP}$  = 10A, 10/1000µs.
- The D.U.T. will come back to the off-state within a duration of 50ms max.

#### TEST CIRCUIT FOR V<sub>FP</sub> AND V<sub>DGL</sub> PARAMETERS



	Pulse	e (µs)	Vp	<b>C</b> <sub>1</sub>	C <sub>2</sub>	L	R <sub>1</sub>	R <sub>2</sub>	R <sub>3</sub>	R <sub>4</sub>	IPP	Rs
	tr	tp	(∨)	(μF)	(nF)	(µH)	(Ω)	(Ω)	(Ω)	(Ω)	(A)	(Ω)
$\bigcirc$	10	700	1500	20	200	0	50	15	25	25	30	10
	1.2	50	1500	1	33	0	76	13	25	25	30	10
	2	10	2500	10	0	1.1	1.3	0	3	3	38	62

# **TECHNICAL INFORMATION**

Fig. A1: LCP1521 concept behavior.



Figure A1 shows the classical protection circuit using the LCP1521 crowbar concept. This topology has been developed to protect the new high voltage SLIC's. It allows to program the negative firing threshold while the positive clamping value is fixed at GND.

When a negative surge occurs on one wire (L1 for example) a current IG flows through the base of the transistor T1 and then injects a current in the gate of the thyristor Th1. Th1 fires and all the surge current flows through the ground. After the surge when the current flowing through Th1 becomes less negative than the holding current  $I_H$ , then Th1 switches off.

When a positive surge occurs on one wire (L1 for example) the diode D1 conducts and the surge current flows through the ground.





In order to minimize the remaining voltage across the SLIC inputs during the surge, the TIP and RING pins of the LCP1521 are doubled (Pins 1 and 8 for TIP / Pins 4 and 5 for RING).

This fact allows the board designer to connect the tracks like in figure A2. With such a PCB design, the extra voltages caused by track stray inductance remain located on the line side of the LCP and do not affects the SLIC side.

The capacitor C is used to speed up the crowbar structure firing during the fast surge edges.

This allows to minimize the dynamical breakover voltage at the SLIC Tip and Ring inputs during fast strikes. Note that this capacitor is generally present around the SLIC - Vbat pin.

So to be efficient it has to be as close as possible from the LCP1521 Gate pin and from the reference ground track (or plan) (see Fig. A2). The optimized value for C is 220nF.

**/** 

The series resitors Rs1 and Rs2 designed in figure A1 represent the fuse resistors or the PTC which are mandatory to withstand the power contact or the power induction tests imposed by the various country standards. Taking into account this fact the actual lightning surge current flowing through the LCP is equal to:

I surge = V surge / (Rg + Rs)

With V surge = peak surge voltage imposed by the standard.

Rg = series resistor of the surge generator

Rs = series resistor of the line card (e.g. PTC)

e.g. For a line card with  $30\Omega$  of series resistors which has to be qualified under GR1089 Core 1000V  $10/1000\mu$ s surge, the actual current through the LCP1521 is equal to:

I surge = 1000 / (10 + 30) = 25A

The LCP1521 is particularly optimized for the new telecom applications such as the fiber in the loop, the WLL, the remote central office. In this case, the operating voltages are smaller than in the classical system. This makes the high voltage SLICs particularly suitable. The schematics of figure A3 gives the most frequent topology used for these applications.

Fig. A3: Protection of high voltage SLIC.



Fig. 1: Surge peak current versus overload duration.

**Fig. 2:** Relative variation of holding current versus junction temperature



#### PACKAGE MECHANICAL DATA





					DIMEN	SIONS	;			
		REF.	Mi	llimetr	es		Inches	5		
			Min.	Тур.	Max.	Min.	Тур.	Max.		
		А			1.75			0.069		
		a1	0.1		0.25	0.004		0.010		
a3 ⊥		a2			1.65			0.065		
b1		a3	0.65		0.85	0.025		0.033		
		b	0.35		0.48	0.014		0.019		
		b1	0.19		0.25	0.007		0.010		
		С	0.25	0.50	0.50	0.010		0.020		
	c1				45° (typ)					
		D	4.8		5.0	0.189	4	0.197		
		Е	5.8		6.2	0.228	10	0.244		
		е		1.27			0.050			
		e3		3.81		LU	0.150			
		F	3.8		4.0	0.15		0.157		
		L	0.4		1.27	0.016		0.050		
		М		0.	0.6			0.024		
		S	10		8° (r	nax)				
(	0	05	2/0							
		Woid	nht Baca				alivory	mada		

Order code	Marking	Package	Weight	Base qty	Delivery mode
LCP1521	151DHV	SO-8	0.08 g	100	Tube
LCP1521RL	151DHV	SO-8	0.08 g	2000	Tape & Reel

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